Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	335	magnetic and memory and (resistance with value) and (non-magnetic with layer) and magnetoresistive and (magnetic with (free layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:13
L2	1	1 and (spinned with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:11
L3	318	1 and (magnetic with field)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:11
L4	7	1 and yoda-hiroaki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:12
L5	1	3 and (insulated-gate with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:13
L6	8	3 and (insulate$4 with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:13
L7	13	1 and (insulate$4 with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:13
L8	1	4 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:13

L9	8	3 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:13
L10	188	magnetic and memory and (resistance with value) and (non-magnetic with layer) and magnetoresistive and (magnetic with (free near layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:14
L11	225	magnetic and memory and (resistance with value) and (non-magnetic with layer) and magnetoresistive and (magnetic with (free same layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:14
L12	75	11 and (write with (magnetic same field))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:15
L13	157	1 and "365"/$7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:15
L14	49	13 and 12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:15
L15	19	14 and (current same magnitude)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:15
L16	15	15 and (desired or predetermined)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:16

L17	0	(magnetic and memory and "0" and "1" and (resistance with value) and (non-magnetic with layer) and magnetoresistive and variable and (free with layer) and (spinned with layer) and (insulated-gate with transistor) and (channel with current) and ((desired or predetermin$4) with magnitude)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:20
L18	0	(magnetic and memory and "0" and "1" and (resistance with value) and (non-magnetic with layer) and magnetoresistive and variable and (free with layer) and (spinned with layer) and (insulated-gate with transistor) and (channel with current)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:21
L20	0	(magnetic and memory and (resistance with value) and (non-magnetic with layer) and magnetoresistive and variable and (free with layer) and (spinned with layer) and (insulated-gate with transistor) and (channel with current)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 11:21